1. (25%) Assume that all transistors are matched. The circuit acts as an amplifier. Let  $K_n$  and  $K_p$  denote the conduction parameter for NMOS and PMOS, and  $\lambda_n$  and  $\lambda_p$  the channel-length modulation parameter for NMOS and PMOS, respectively. Show that the voltage gain is

$$A_{v} = \frac{V_{o}}{V_{i}} \approx \frac{-4K_{n}}{I_{REF}(\lambda_{n}^{2} + \lambda_{p}^{2})}$$



2. (30%) Assume that all transistors are matched. Neglect base currents and assume  $V_A = \infty$ .

- (a) Derive the expression for  $I_o$  in terms of  $I_{REF}$  and  $R_E$ .
- (b) Determine the value of  $R_E$  such that  $I_O = I_{REF} = 100 \mu A$ . Assume  $V_{BE} = 0.7V$  at a collector current of 1 mA.



3. (20%) The circuit is biased at  $V^+ = +5V$  and  $V^- = -5V$ . The transistor parameters are:

 $V_{TP} = -1.2V, k'_{p} = 80 \,\mu A/V^{2}, \lambda = 0, (W/L)_{1} = (W/L)_{2} = 25, \text{ and}$  $(W/L)_{3} = (W/L)_{4} = 4.$  Determine  $I_{REF}, I_{O}$  and  $V_{SD2}$  (sat).



4. (25%) Assume transistor parameters are  $\beta = 120$  and  $V_A = 80V$ . The  $V_{BB}$  voltage is such that all transistors are biased in the active region. Determine the small-signal voltage gain  $A_v = v_o / v_i$ .



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